

1N5059 1N5061
1N5060 1N5062

GLASS PASSIVATED
SILICON RECTIFIERS
1.0 AMP, 200 THRU 800 VOLT



GPR-1A CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 1N5059 series types are silicon rectifiers manufactured in a hermetically sealed, glass passivated package, designed for general purpose applications where high reliability is desired. Higher voltage devices are available in the CPR1-010 series.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

	SYMBOL	1N5059	1N5060	1N5061	1N5062	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	200	400	600	800	V
DC Blocking Voltage	V_R	200	400	600	800	V
RMS Reverse Voltage	$V_{R(RMS)}$	140	280	420	560	V
Average Forward Current ($T_A=75^{\circ}\text{C}$)	I_O			1.0		A
Peak Forward Surge Current, $t_p=8.3\text{ms}$	I_{FSM}			40		A
Operating and Storage Junction Temperature	T_J, T_{stg}		-65 to +175			$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}		40			$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

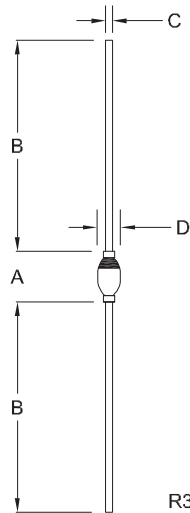
SYMBOL	TEST CONDITIONS	MAX	UNITS
I_R	$V_R=\text{Rated } V_{RRM}$	5.0	μA
I_R	$V_R=\text{Rated } V_{RRM}, T_A=175^{\circ}\text{C}$ (1N5059, 1N5060)	300	μA
I_R	$V_R=\text{Rated } V_{RRM}, T_A=175^{\circ}\text{C}$ (1N5061, 1N5062)	200	μA
V_F	$I_F=1.0\text{A}$	1.2	V
C_J	$V_R=4.0\text{V}, f=1.0\text{MHz}$	15	pF

1N5059 1N5061
1N5060 1N5062

GLASS PASSIVATED
SILICON RECTIFIERS
1.0 AMP, 200 THRU 800 VOLT



GPR-1A CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	-	0.240	-	6.10
B	1.000	-	25.40	-
C	0.028	0.034	0.71	0.86
D	0.070	0.150	1.80	3.81

GPR-1A (REV: R3)

MARKING: FULL PART NUMBER

R5 (28-February 2013)